

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Kuniaki YAGI, et al.

Appln. No.: Not Yet Assigned

Confirmation No.: Not Yet Assigned

Group Art Unit: Not Yet Assigned

Filed: January 18, 2002

Examiner: Not Yet Assigned

For: SINGLE CRYSTAL SiC AND METHOD OF PRODUCING THE SAME AS WELL AS
SiC SEMICONDUCTOR DEVICE AND SiC COMPOSITE MATERIAL

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

6. A single crystal SiC, wherein:

the single crystal SiC is obtained by a method claimed in claim 1, and

the planar defect density of a topmost surface falls within a range not higher than $10^3/\text{cm}^2$.

7. A single crystal SiC, comprising:

single crystal SiC obtained by a method claimed in claim 1, and

another SiC deposited on the single crystal SiC by the vapor phase growth method or the

liquid phase growth method.

10. A SiC composite material, comprising:

single crystal SiC produced by a method claimed in claim 1, and

diamond or GaN formed on the single crystal SiC.

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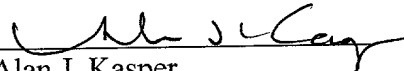
PRELIMINARY AMENDMENT
Attorney Docket No.: Q68148

REMARKS

Accordingly, early and favorable consideration of the presently pending claims is respectfully requested.

Respectfully submitted,

SUGHRUE MION, PLLC
2100 Pennsylvania Avenue, N.W.
Washington, D.C. 20037-3213
Telephone: (202) 293-7060
Facsimile: (202) 293-7860
AJK/rwl
Date: January 18, 2002


Alan J. Kasper
Registration No. 25,426

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APPENDIX

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The claims are amended as follows:

6. A single crystal SiC, wherein:
the single crystal SiC is obtained by a method claimed in ~~any one of claims 1 through 5~~,
and
the planar defect density of a topmost surface falls within a range not higher than $10^3/\text{cm}^2$.
7. A single crystal SiC, comprising:
single crystal SiC obtained by a method claimed in ~~any one of claims 1 through 5~~, and
another SiC deposited on the single crystal SiC by the vapor phase growth method or the
liquid phase growth method.
10. A SiC composite material, comprising:
single crystal SiC produced by a method claimed in ~~any one of claims 1 through 5~~, and
diamond or GaN formed on the single crystal SiC.